

Please replace the Abstract with the following new Abstract:

**ABSTRACT**

-- A memory includes a first electrode film, a storage material film formed on the first electrode film, provided with a storage part and a thin-film part having a thickness smaller than a thickness of the storage part and which is at least about 15% of the thickness of the storage part on average, a second electrode film formed on the storage part of the storage material film. The thickness of the thin-film part may be between 15% and 95% of the thickness of the storage part. An insulator film may be formed on the thin-film part and the second electrode part, the insulator film formed on the thin-film part having a same pattern as the thin-film part. --